

Ordering number : ENA0826



SANYO Semiconductors

## DATA SHEET

# 2SK4123LS — N-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- Adoption of high reliability HVP process.
- Attachment workability is good by Mica-less package.
- Avalanche resistance guarantee.

### Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		450	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±30	V
Drain Current (DC)	I <sub>DC</sub> *1	Limited only by maximum temperature	18	A
	I <sub>Dpack</sub> *2	SANYO's ideal heat dissipation condition	12.4	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	66	A
Allowable Power Dissipation	P <sub>D</sub>		2.0	W
		Tc=25°C (SANYO's ideal heat dissipation condition)	40	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C
Avalanche Energy (Single Pulse) *3	E <sub>AS</sub>		412	mJ
Avalanche Current *4	I <sub>AV</sub>		18	A

\*1 Shows chip capability

\*2 Package limited

\*3 V<sub>DD</sub>=99V, L=2mH, I<sub>AV</sub>=18A

\*4 L≤2mH, single pulse

Marking : K4123

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# 2SK4123LS

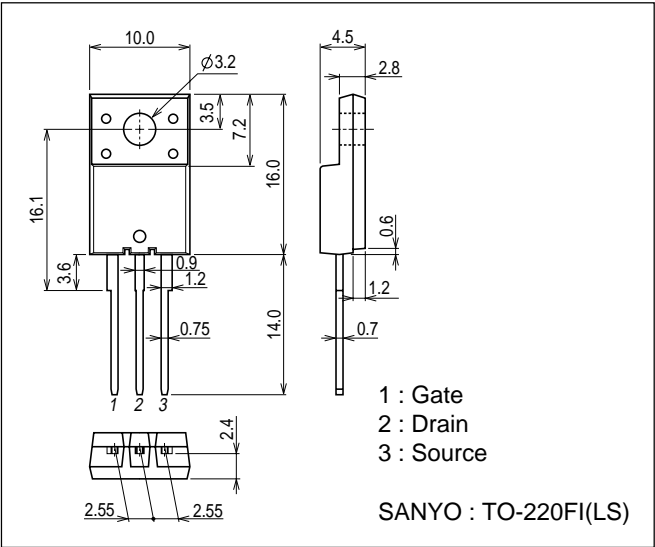
## Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=10mA, V_{GS}=0V$	450			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=360V, V_{GS}=0V$			100	$\mu A$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 30V, V_{DS}=0V$			$\pm 100$	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	3		5	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=9A$	4.5	9		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=9A, V_{GS}=10V$		0.26	0.34	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS}=30V, f=1MHz$		1200		pF
Output Capacitance	$C_{oss}$	$V_{DS}=30V, f=1MHz$		280		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=30V, f=1MHz$		60		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		28		ns
Rise Time	$t_r$	See specified Test Circuit.		97		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit.		140		ns
Fall Time	$t_f$	See specified Test Circuit.		56		ns
Total Gate Charge	$Q_g$	$V_{DS}=200V, V_{GS}=10V, I_D=18A$		47.2		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=200V, V_{GS}=10V, I_D=18A$		7.8		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=200V, V_{GS}=10V, I_D=18A$		28.4		nC
Diode Forward Voltage	$V_{SD}$	$I_S=18A, V_{GS}=0V$		0.9	1.2	V

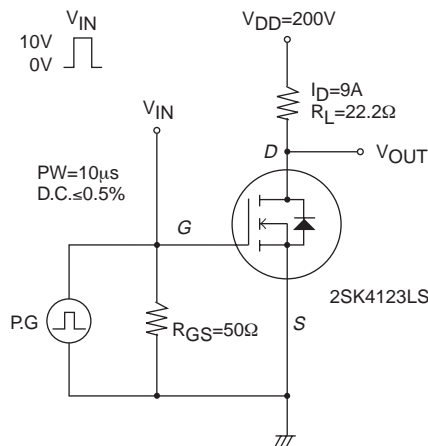
## Package Dimensions

unit : mm (typ)

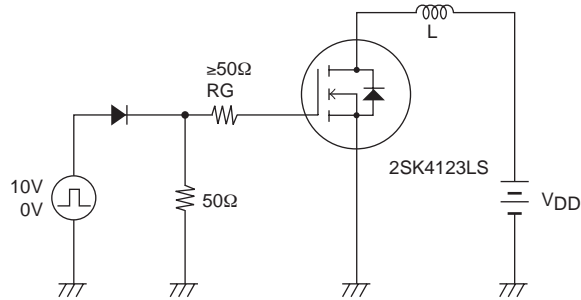
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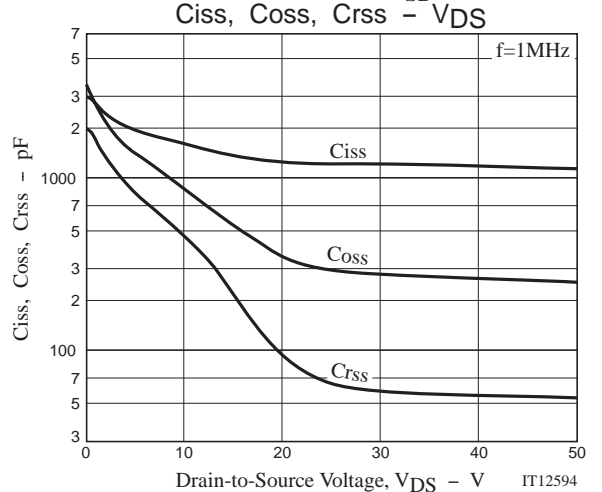
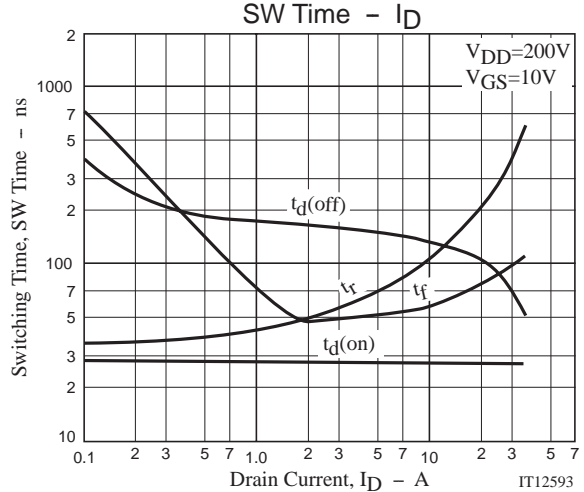
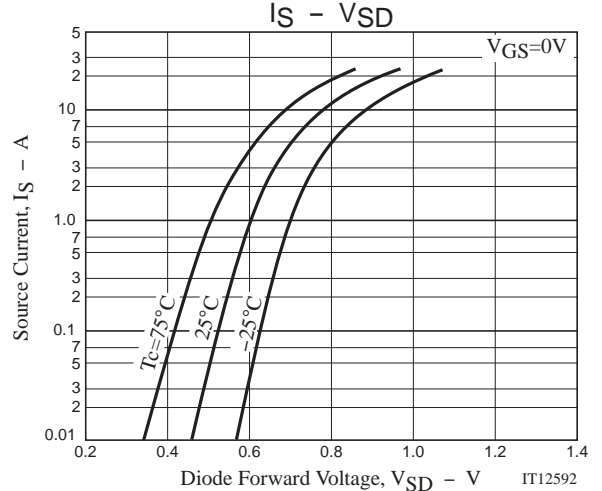
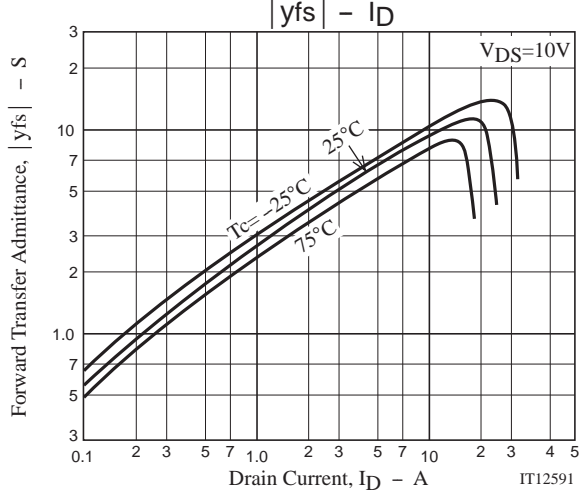
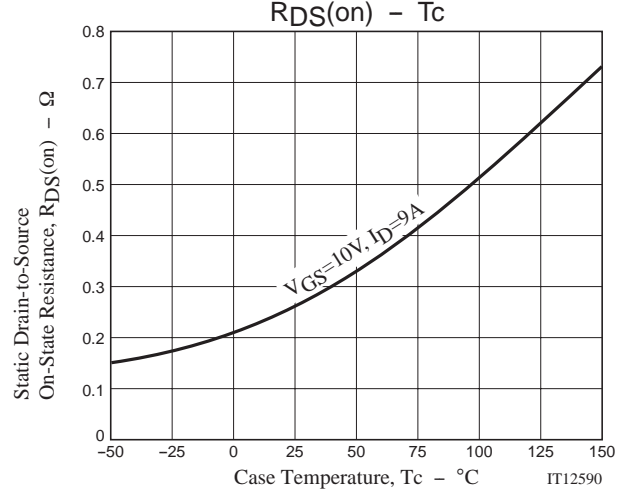
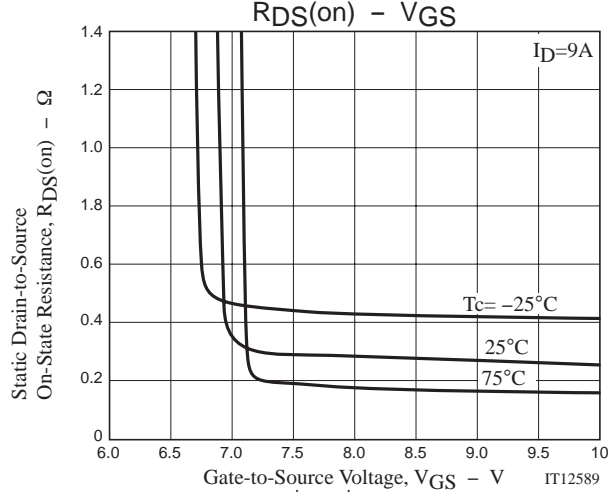
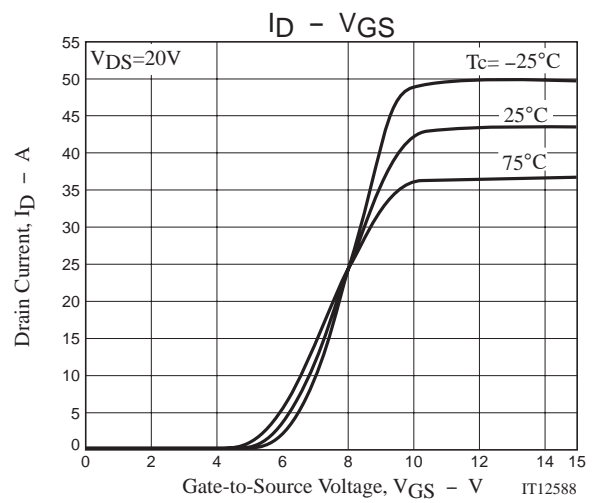
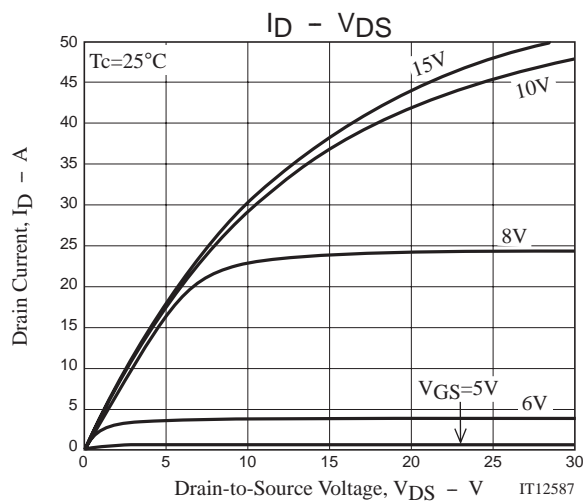
## Switching Time Test Circuit



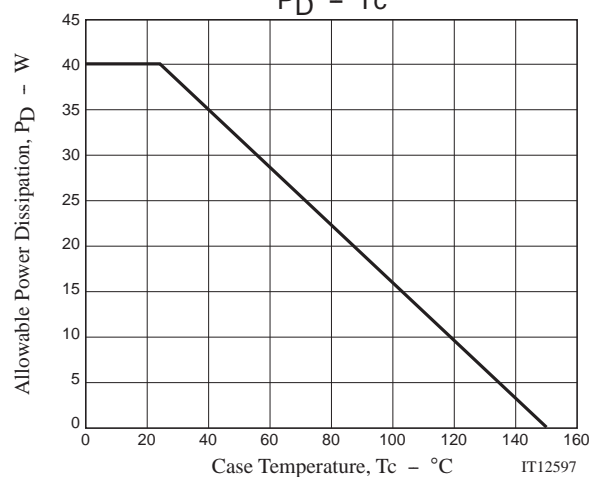
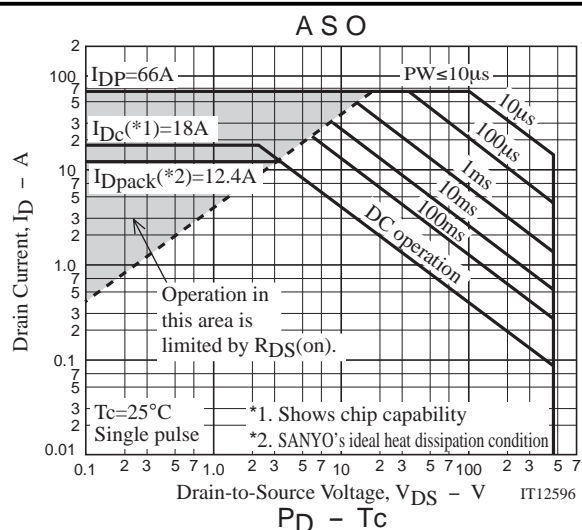
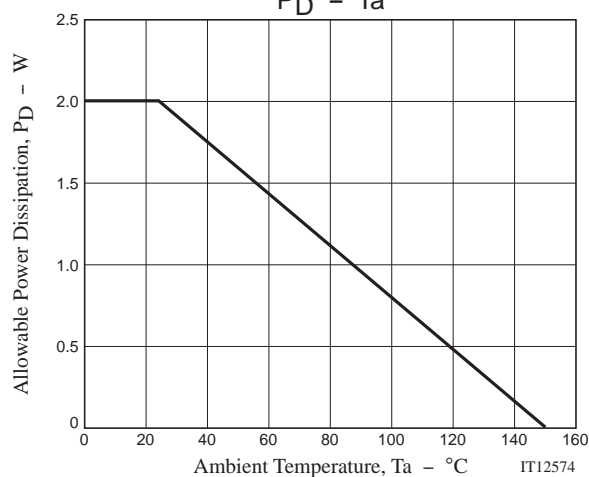
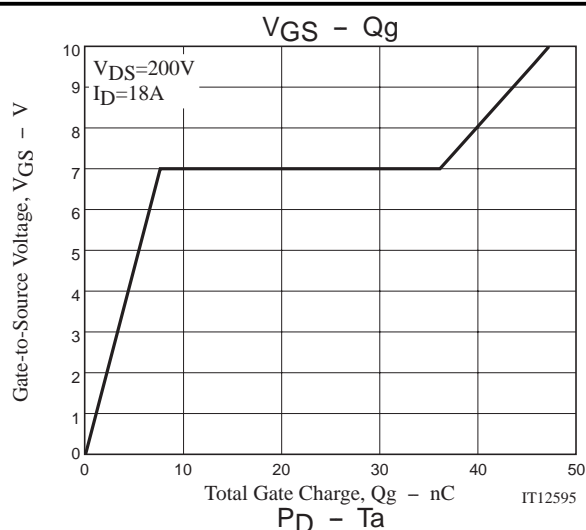
## Avalanche Resistance Test Circuit



2SK4123LS



## 2SK4123LS



Note on usage : Since the 2SK4123LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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